

General Description

The ZM160N04D combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for load switch and battery protection applications.

Features

Advance high cell density Trench technology
 $R_{DS(ON)}$ to minimize conductive loss
 fast switching

Product Summary

Application

nd Synchronous Rectifier

Ordering Information:

Part NO.	ZM160N04D
Marking	

Absolute Maximum Ratings $T_C = 25$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_{D@TC=25^{\circ}C}$	35	A
	$I_{D@TC=75^{\circ}C}$	26.6	A
	$I_{D@TC=100^{\circ}C}$	22.1	A
Pulsed Drain Current ①	I_{DM}	80	A
Total Power Dissipation	$P_D@TC=25^{\circ}C$	85	W
Total Power Dissipation	$P_D@TA=25^{\circ}C$	3.5	W
Operating Junction Temperature	T_J	-55 to 150	$^{\circ}C$
Storage Temperature	T_{STG}	-55 to 150	$^{\circ}C$





Fig.7 Switching Time Measurement Circuit

Fig.8 Gate Charge Waveform

Fig.9 Switching Time Measurement Circuit

Fig.10 Gate Charge Waveform

Fig.11

Dimensions (TO-252)

Unit mm

SYMBOL	min	max	SYMBOL	min	max
A	2.10	2.50	B	0.85	1.25
b	0.50	0.80	b1	0.50	0.90
b2	0.45	0.70	C	0.45	0.70
D	6.30	6.75	D1	5.10	5.50
E	5.30	6.30	e1	2.25	2.35
L1	9.20	10.60	e2	4.45	4.75
L2	0.90	1.75	L3	0.60	1.10
K	0.00	0.23			

